# 捷多邦,专业PCB打样工厂,24小时加急出货

## **MMBTA56WT1**

# **Driver Transistor**

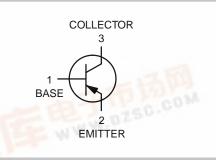
## **PNP Silicon**

Moisture Sensitivity Level: 1 ESD Rating: Human Body Model - 4 kV Machine Model - 400 V WWW.DZSC.COM



### **ON Semiconductor**<sup>®</sup>

http://onsemi.com





## MARKING DIAGRAM



FM = Specific Device Code D = Date Code

### ORDERING INFORMATION

Device	Package	Shipping
MMBTA56WT1	SC-70	3000/Tape & Reel



Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	-80	Vdc
Collector–Base Voltage	V <sub>CBO</sub>	-80	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-4.0	Vdc
Collector Current – Continuous	Ι <sub>C</sub>	-500	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board $T_A = 25^{\circ}C$	P <sub>D</sub>	150	mW
Thermal Resistance, Junction to Ambient	$R_{\thetaJA}$	833	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

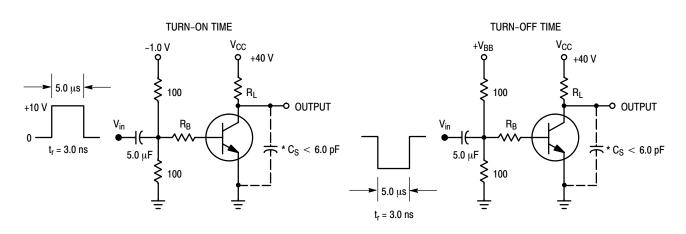


### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 1) $(I_C = -1.0 \text{ mAdc}, I_B = 0)$	V <sub>(BR)CEO</sub>	-80	-	Vdc
Emitter–Base Breakdown Voltage ( $I_E = -100 \ \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	-4.0	-	Vdc
Collector Cutoff Current ( $V_{CE} = -60 \text{ Vdc}, I_B = 0$ )	I <sub>CES</sub>	_	-0.1	μAdc
Collector Cutoff Current $(V_{CB} = -60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -80 \text{ Vdc}, I_E = 0)$	I <sub>CBO</sub>	_	_ _0.1	μAdc
ON CHARACTERISTICS			1	•
DC Current Gain ( $I_C = -10 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}$ ) ( $I_C = -100 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}$ )	h <sub>FE</sub>	100 100		-
Collector–Emitter Saturation Voltage ( $I_C = -100 \text{ mAdc}, I_B = -10 \text{ mAdc}$ )	V <sub>CE(sat)</sub>	_	-0.25	Vdc
Base–Emitter On Voltage ( $I_C = -100 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}$ )	V <sub>BE(on)</sub>	_	-1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				•
Current–Gain – Bandwidth Product (Note 2)	f <sub>T</sub>	50	-	MHz

### (I<sub>C</sub> = -100 mAdc, V<sub>CE</sub> = -1.0 Vdc, f = 100 MHz)

1. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.2. f<sub>T</sub> is defined as the frequency at which |h<sub>fe</sub>| extrapolates to unity.



\*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

#### Figure 1. Switching Time Test Circuits

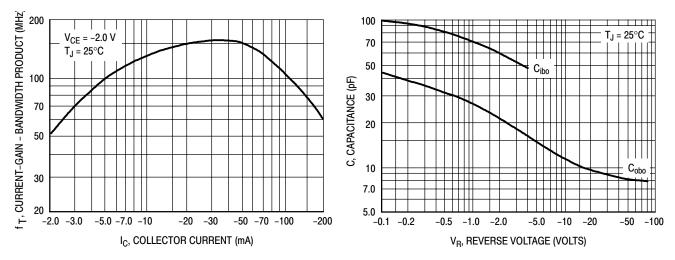


Figure 2. Current–Gain — Bandwidth Product



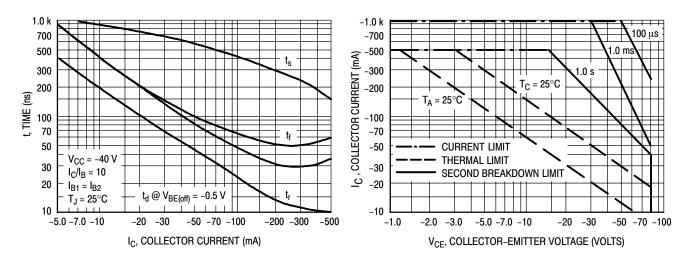
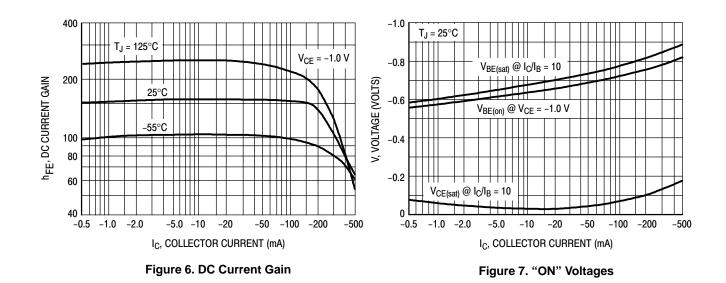


Figure 4. Switching Time

Figure 5. Active–Region Safe Operating Area



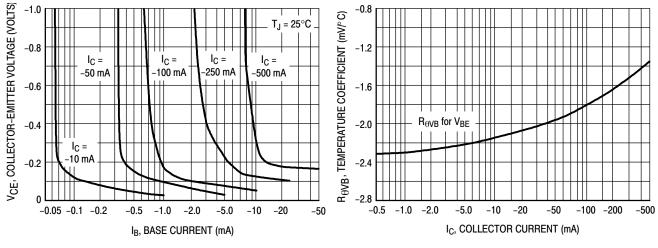


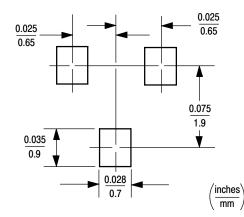
Figure 8. Collector Saturation Region

Figure 9. Base–Emitter Temperature Coefficient

### **INFORMATION FOR USING THE SC-70/SOT-323 SURFACE MOUNT PACKAGE**

#### MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



### SC-70/SOT-323 POWER DISSIPATION

The power dissipation of the SC–70/SOT–323 is a function of the pad size. This can vary from the minimum pad size for soldering to the pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by  $T_{J(max)}$ , the maximum rated junction temperature of the die,  $R_{\theta JA}$ , the thermal resistance from the device junction to ambient; and the operating temperature,  $T_A$ . Using the values provided on the data sheet,  $P_D$  can be calculated as follows.

$$P_{D} = \frac{T_{J(max)} - T_{A}}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values

### SOLDERING PRECAUTIONS

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.\*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference should be a maximum of 10°C.

into the equation for an ambient temperature  $T_A$  of 25°C, one can calculate the power dissipation of the device which in this case is 150 milliwatts.

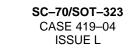
$$P_{D} = \frac{150^{\circ}C - 25^{\circ}C}{833^{\circ}C/W} = 150 \text{ milliwatts}$$

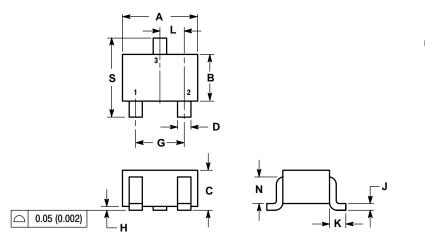
The 833°C/W assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 150 milliwatts. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad<sup>®</sup>. Using a board material such as Thermal Clad, a higher power dissipation can be achieved using the same footprint.

- The soldering temperature and time should not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient should be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling

\* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

### PACKAGE DIMENSIONS





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.032	0.040	0.80	1.00	
D	0.012	0.016	0.30	0.40	
G	0.047	0.055	1.20	1.40	
Н	0.000	0.004	0.00	0.10	
J	0.004	0.010	0.10	0.25	
K	0.017 REF		0.425 REF		
L	0.026 BSC 0.028 REF		0.650 BSC		
Ν			0.700 REF		
S	0.079	0.095	2.00	2.40	

STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR

## <u>Notes</u>

Thermal Clad is a registered trademark of the Bergquist Company.

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